

**Plastic Package** 

# PNP SILICON PLANAR DARLINGTON POWER TRANSISTOR

# BDW47

**TO-220** 

B<sup>C</sup>C C

# **General Purpose and Low Speed Switching Application**

## **Complementary BDW42**

#### **ABSOLUTE MAXIMUM RATINGS**

DESCRIPTION	SYMBOL	VALUE	UNIT	
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V	
Collector-Base Voltage	V <sub>CBO</sub>	100	V	
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V	
Collector Current Continuous	I <sub>C</sub>	15	А	
Base Current	Ι <sub>Β</sub>	0.5	А	
Total Device Dissipation @ T <sub>c</sub> =25ºC Derate above 25ºC	PD	85 0.68	W W/ºC	
Operating And Storage Junction Temperature Range	T <sub>j,</sub> T <sub>stg</sub>	- 55 to +150	°C	

#### THERMAL RESISTANCE

Junction to CaseR1.47°C/W
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DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Emitter Sustaining Voltage	$^{*}V_{\text{CEO}(\text{sus})}$	I <sub>C</sub> =30mA, I <sub>B</sub> =0	100		V
Collector Cutoff Current	I <sub>CEO</sub>	$V_{CE}$ =50V, $I_{B}$ =0		2.0	mA
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =100V, I <sub>E</sub> =0		1.0	mA
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{BE}$ =5.0V, I <sub>C</sub> =0		2.0	mA
DC Current Gain	*h <sub>FE</sub>	I <sub>C</sub> =5.0A, V <sub>CE</sub> =4.0V	1000		
		I <sub>C</sub> =10A, V <sub>CE</sub> =4.0V	250		
Collector Emitter Saturation Voltage	*V <sub>CE (sat)</sub>	I <sub>C</sub> =5.0A, I <sub>B</sub> =10mA		2.0	V
		I <sub>C</sub> =10A, I <sub>B</sub> =50mA		3.0	V
Base Emitter On Voltage	*V <sub>BE (on)</sub>	I <sub>C</sub> =10A, V <sub>CE</sub> =4.0V		3.0	V

#### SECOND BREAKDOWN

Second Breakdown Collector Current	**	$V_{CE} = 22.5V$	3.8	А
with Base Forward Biased		V <sub>CE</sub> = 36V	1.2	A

## **DYNAMIC CHARACTERISTICS**

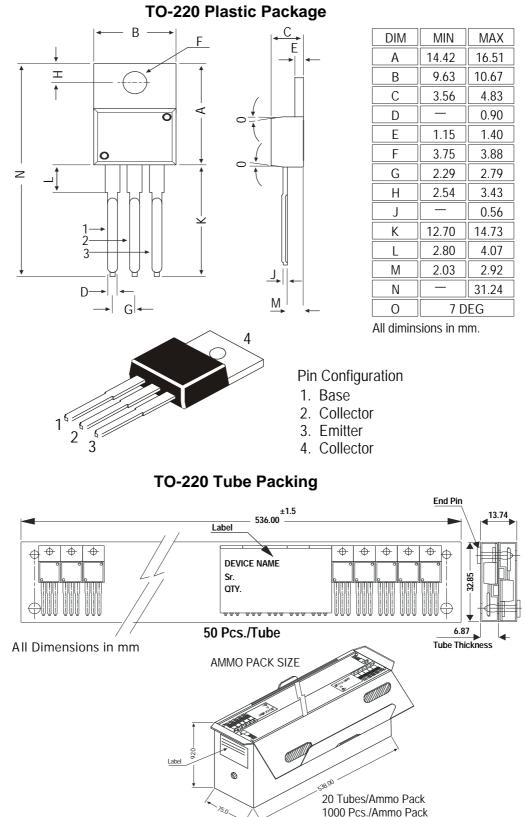
Transition Frequency	f <sub>T</sub>	$I_{C}$ =3.0A, $V_{CE}$ =3.0V, f=1MHz	4.0		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz		300	рF
Small-Signal Current Gain	h <sub>fe</sub>	I <sub>C</sub> =3.0A, V <sub>CE</sub> =3.0V, f=1kHz	300		

\* Pulse test : Pulse Width =300ms, Duty Cycle = 2.0%

\*\* Pulse test non repetitive : Pulse Width = 250 ms

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# TO-220 Plastic Package



## **Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-220	200 pcs/polybag 50 pcs/tube	396 gm/200 pcs 120 gm/50 pcs	3" x 7.5" x 7.5" 3.5" x 3.7" x 21.5"	1.0K 1.0K	17" x 15" x 13.5" 19" x 19" x 19"	16.0K 10.0K	36 kgs 29 kgs

#### BDW47Rev140803E

Continental Device India Limited

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TO-220

#### Disclaimer

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